

Ref. 2811 #2/IOS
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November 17, 1999

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

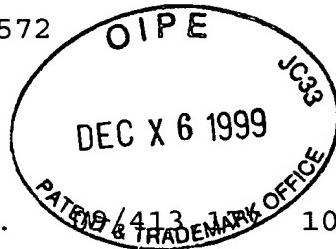
Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

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TECHNOLOGY CENTER 2800



Serial No. 10/07/99

Lap Chan, K.W. J. Chew, C.L. Cha,
C.T. ChuaA METHOD TO FABRICATE HORIZONTAL
AIR COLUMNS UNDERNEATH METAL
INDUCTOR

Grp. Art Unit: 2811

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,828,121 to Lur et al., "Multi-Level
Conduction Structure for VLSI Circuits", discloses air gaps
between metal lines at different levels by etching the
dielectric layers between the metal line levels.

The following two U.S. Patents describe air gaps under inductors:

- 1) U.S. Patent 5,539,241 to Abidi et al., "Monolithic Passive Component".
- 2) U.S. Patent 5,844,299 to Merrill et al., "Integrated Inductor".

U.S. Patent 5,880,026 to Xing et al., "Method for Air Gap Formation by Plasma Treatment of Aluminum Interconnects", discloses a process to form air gaps between conductors.

U.S. Patent 5,880,018 to Boeck et al., "Method for Manufacturing a Low Dielectric Constant Inter-Level Integrated Circuit Structure", discloses an air gap process between lines.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37661